SE307-C

GaAs INFRARED EMITTING DIODE

DESCRIPTION

The SE307-C is a GaAs (Gallium Arsenide) Infrared Emitting Diode which is mounted on the lead frames and molded in plastic. On forward bias, it emits a spectrally narrow band of radiation peaking at 940 nm.

PACKAGE DIMENSIONS in millimeters Dark blue Clear Plastic Resin 0.8 A(1.05) B(0.6) A: \$\phi\$ 1.2 MAX. B: \$\phi\$ 0.8 MAX. A(1.05) A: \$\phi\$ 1.2 MAX. A: \$\phi\$ 1.2 MAX. A: \$\phi\$ 1.2 MAX. A: \$\phi\$ 1.4 MAX. A: \$\phi\$ 1.5 MAX. A: \$\phi\$ 1.5 MAX. A: \$\phi\$ 1.5 MAX.

FEATURES

• Economical.

30E D

- High output power.
- Long Life.
- Good linearity.
- Spectrally matched to silicon sensors.
- Long lead.

APPLICATIONS

- Paper Tape and Punch Card Readers.
- Light source for smoke detector.
- Optical encoders.
- Photochoppers, Isolator.
- Light source for remote control.

ABSOLUTE MAXIMUM RATINGS

Maximum Power Dissipation (T _a = 25 °C)	₽	150	mW
Maximum Forward Current (T _a = 25 °C)	l _F	100	mΑ
Maximum Pulse Forward Current (Ta = 25 °C)	lep*	1.0	Α
Maximum Reverse Voltage (T _a = 25 °C)	VR	5.0 [']	٧
Maximum Temperatures			
Junction Temperature	T _i	+100	°C
Storage Temperature	Tsta	-40 to +100	°C
Operating Temperature	Tont	-30 to +85	°C

ELECTRO-OPTICAL CHARACTERISTICS (Ta = 25 °C)

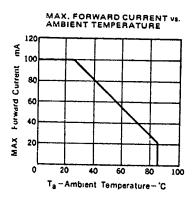
2. Cathode

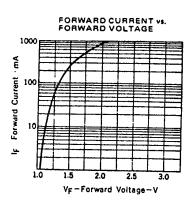
CHARACTERISTIC	SYMBOL	MIN.	TYP	MAX.	UNIT	TEST CONDITIONS
Forward Voltage	VF		1.25	1.4	i V	lp = 50 mA
Pulse Forward Voltage	VFP*		2.1	2.6	: V	
Capacitance	Ct		: 40	L	! pF	V = 0, f = 1.0 MHz
Peak Emission Wavelength	^{\(\lambda\)} peak		940	,	nm	IF = 50 mA
Spectral Line Half Width	λ		50		nm	I _F = 50 mA
Output Power	l _e	20	30	1	mW/sr	: lr = 50 mA
Light Turn-On and Turn-Off	ton-toff		1		μs	:

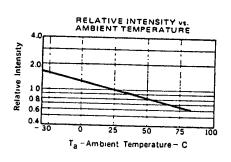
^{*} f = 1.0 kHz, Duty Cycle 1 %

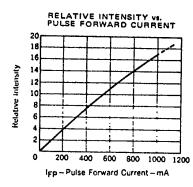
T-41-11

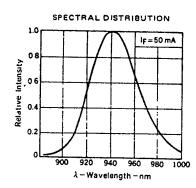
TYPICAL CHARACTERISTICS (Ta = 25 °C)

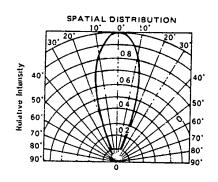












HANDLING PRECAUTIONS:

- 1. The full resin-molded LED lamps have generally a little mechanical and thermal strength than other resin-molded semiconductor devices as they have less additives. Therefore please note on the following points.
 - Soldering of leads should be made at the point 5 mm or more from the root of the leads at 260 $^{\circ}$ C and within 5 s.
 - If the temperature of the molded portion rises in addition to the residual stress between the leads, the possibility that open or short circuit occurs due to the deformation or destruction of the resin will increase.

2. On cleaning the device:

Cleaning with unsuitable solvent may impair the resin of the package and the following solvents should be used at the temperature of less than 45 $^{\circ}$ C and for less than 3 minutes of immersion time.

Ethanol, Methanol

Isopropyl-alcohol

(b) Ultrasonic cleaning will add some stress on devices. The degree of the stress differs depending on the oscillation output power, the size of the PCB and the mounting methods of the devices, therefore it should be confirmed by making an experiment at actual conditions that the cleaning does not have any problem on the devices.